Claims

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- A method of producing a hard metal film by cathode sputtering comprising the steps of:
- a. placing a substrate in an evacuated chamber comprising an atmosphere comprising inert gas and a reactive gas; and
- b. sputtering a metal cathode target wherein the concentration of reactive gas is sufficiently low that the metal is sputtered in the metallic mode to deposit a metal film.
- 2. A method according to claim 1, wherein the metal is selected from the group consisting of titanium, zirconium, tantalum, hafnium, niobium, vanadium and mixtures thereof.
- 3. A method according to claim 2, wherein the metal is selected from the group consisting of titanium and zirconium.
- 4. A method according to claim 3, wherein the metal is titanium.
 - 5. A method according to claim 1, wherein the reactive gas is selected from the group consisting of oxygen and nitrogen.
 - 6. A method according to claim 5, wherein the reactive gas is oxygen.
 - 7. A method according to claim 1, wherein the inert gas is argon.

- 8. A method according to claim 7, wherein the atmosphere comprises argon and up to 30 percent oxygen.
- 9. A method according to claim 1, comprising the further step of thermally oxidizing the metal film.
- 10. A method according to claim 9, comprising the further step of depositing a metal oxide layer over the metal film prior to the step of thermally oxidizing the metal film.
 - 11. A product prepared by the method of claim 1.

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- 12. A product prepared by the method of claim 2, wherein the metal is selected from the group consisting of titanium, zirconium, tantalum, hafnium, niobium, vanadium and mixtures thereof.
 - 13. A product prepared by the method of claim 2, wherein the metal is selected from the group consisting of titanium and zirconium.
 - 14. A product prepared by the method of claim 3, wherein the metal is titanium.
 - 15. A product prepared by the method of claim 1, wherein the reactive gas is selected from the group consisting of oxygen and nitrogen.
 - 16. A product prepared by the method of claim 5, wherein the reactive gas is oxygen.

- 17. A product prepared by the method of claim 1, wherein the inert gas is argon.
- 18. A product prepared by the method of claim 7, wherein the atmosphere comprises argon and up to 30 percent oxygen.
- 19. A product prepared by the method of claim 1, wherein the metal film is thermally oxidized.
- 20. A product prepared by the method of claim 9, further comprising a metal oxide film deposited on the metal film prior to thermal oxidation of the metal film.